

N-channel 30 V 11.6 m Ω logic level MOSFET in LFPAK using NextPower technology

Rev. 3 — 24 October 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads

1.3 Applications

Quick reference data

Table 1.

- DC-to-DC converters
- Load switching

Synchronous buck regulator

1.4 Quick reference data

	Guick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	30	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	-	37	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	29	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 4.5 \text{ V}; \text{ I}_{D} = 10 \text{ A}; \text{ T}_{j} = 25 ^{\circ}\text{C}; \\ \text{see } \overline{\text{Figure 12}} \end{array}$	-	12.3	14.5	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 25 °C; see <u>Figure 12</u>	-	9.9	11.6	mΩ
Dynamic	characteristics					
Q_{GD}	gate-drain charge	V_{GS} = 4.5 V; I _D = 10 A; V _{DS} = 15 V; see Figure 14; see Figure 15	-	1.4	-	nC
Q _{G(tot)}	total gate charge	V_{GS} = 4.5 V; I_D = 10 A; V_{DS} = 15 V; see Figure 14; see Figure 15	-	4.9	-	nC

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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		2
2	S	source	mb	
3	S	source		
4	G	gate	Q;	
mb	D	mounting base; connected to drain	$\begin{array}{c} \hline \\ \hline \\ 1 \\ 2 \\ 3 \\ 4 \\ \end{array}$	mbb076 S

SOT669 (LFPAK; Power-SO8)

3. Ordering information

Table 3. Orderin	information		
Type number	Package		
	Name	Description	Version
PSMN011-30YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

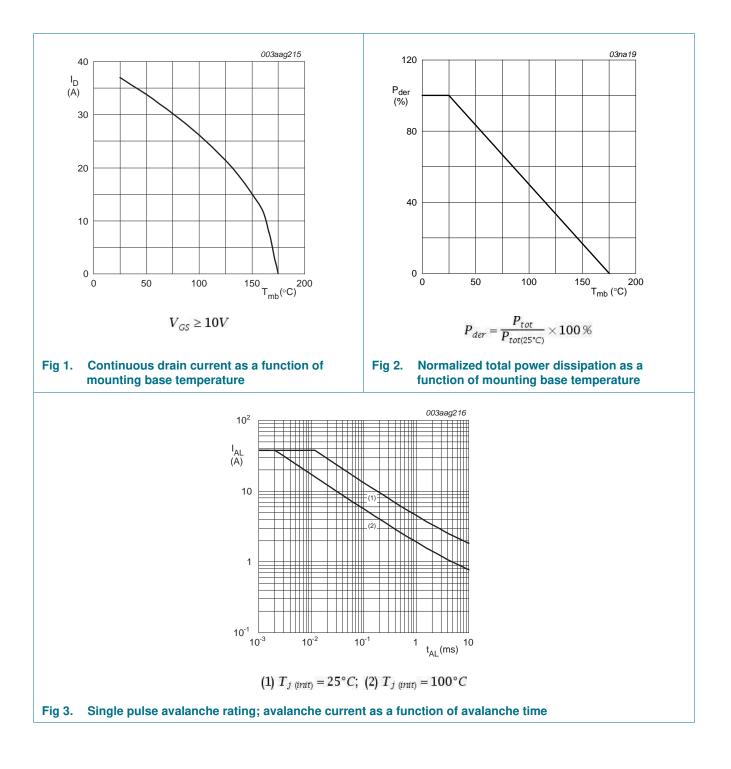
4. Limiting values

Table 4.Limiting values

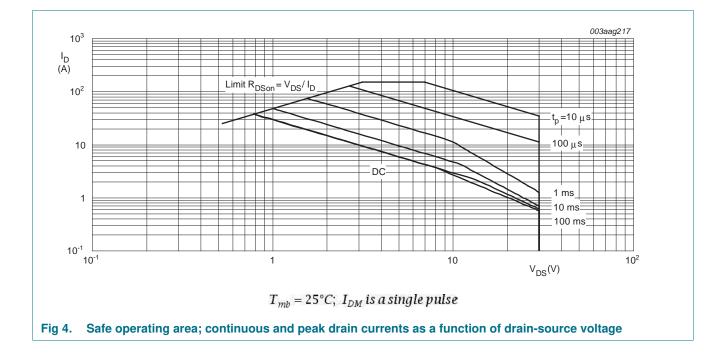
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	30	V
V _{DGR}	drain-gate voltage	25 °C \leq T _j \leq 175 °C; R _{GS} = 20 k Ω	-	30	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	-	37	А
		V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	-	26	А
I _{DM}	peak drain current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C; see <u>Figure 4</u>	-	150	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	29	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	140	-	V
Source-drai	n diode				
I _S	source current	T _{mb} = 25 °C	-	26	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	150	А
Avalanche r	uggedness				
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \text{ V}; \ T_{j(\text{init})} = 25 \ ^{\circ}\text{C}; \ I_{D} = 37 \text{ A}; \\ V_{sup} \leq 30 \text{ V}; \ R_{GS} = 50 \ \Omega; \ unclamped; \\ see \ \underline{Figure \ 3} \end{array} $	-	9	mJ

PSMN011-30YLC



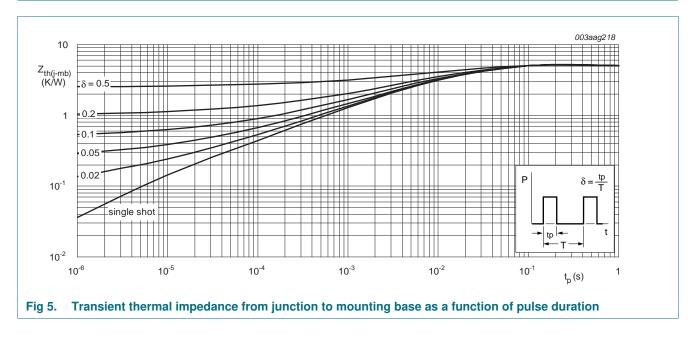
PSMN011-30YLC



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5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 5	-	4.87	5.06	K/W



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6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	30	-	-	V
	voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	1.05	1.57	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μA
I _{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 10 A; T _j = 25 °C; see <u>Figure 12</u>	-	12.3	14.5	mΩ
		V_{GS} = 4.5 V; I_D = 10 A; T_j = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	23.4	mΩ
		V_{GS} = 10 V; I_D = 10 A; T_j = 25 °C; see <u>Figure 12</u>	-	9.9	11.6	mΩ
	V_{GS} = 10 V; I_D = 10 A; T_j = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	18.8	mΩ	
R _G	gate resistance	f = 1 MHz	-	2	4	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14; see Figure 15	-	10.3	-	nC
		<u></u>				
		$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see Figure 14; see Figure 15	-	4.9	-	nC
		$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	4.9 9	-	nC nC
Q _{GS}	gate-source charge	$\begin{split} I_D &= 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \\ \text{see Figure 14}; \text{see Figure 15} \\ I_D &= 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V} \\ I_D &= 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \end{split}$	-			
	gate-source charge pre-threshold gate-source charge	$I_{D} = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see Figure 14; see Figure 15 $I_{D} = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$		9	-	nC
Q _{GS(th)}	pre-threshold gate-source	$\begin{split} I_D &= 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \\ \text{see Figure 14}; \text{see Figure 15} \\ I_D &= 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V} \\ I_D &= 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \end{split}$	-	9 1.5	-	nC nC
Q _{GS(th)} Q _{GS(th-pl)}	pre-threshold gate-source charge post-threshold gate-source	$\begin{split} I_D &= 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \\ \text{see Figure 14}; \text{see Figure 15} \\ I_D &= 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V} \\ I_D &= 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \end{split}$	-	9 1.5 1.1	-	nC nC nC
Q _{GS(th)} Q _{GS(th-pl)} Q _{GD}	pre-threshold gate-source charge post-threshold gate-source charge	$\begin{split} I_D &= 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \\ \text{see Figure 14}; \text{see Figure 15} \\ I_D &= 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V} \\ I_D &= 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \end{split}$	-	9 1.5 1.1 0.4	-	nC nC nC nC
$Q_{GS(th)}$ $Q_{GS(th-pl)}$ Q_{GD} $V_{GS(pl)}$	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge	$\begin{split} I_D &= 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V};\\ \text{see Figure 14}; \text{ see Figure 15}\\ I_D &= 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V}\\ I_D &= 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V};\\ \text{see Figure 14}; \text{ see Figure 15}\\ \end{split}$	-	9 1.5 1.1 0.4 1.4	-	nC nC nC nC
Q _{GS} (th) Q _{GS} (th-pl) Q _{GD} V _{GS} (pl) C _{iss}	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau voltage	$\begin{split} & I_D = 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \\ & \text{see Figure 14}; \text{ see Figure 15} \\ & I_D = 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V} \\ & I_D = 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \\ & \text{see Figure 14}; \text{ see Figure 15} \\ \end{split}$	- - -	9 1.5 1.1 0.4 1.4 2.5		nC nC nC nC v
Q _{GS} (th) Q _{GS} (th-pl) Q _{GD} V _{GS} (pl) C _{iss} C _{oss}	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance	$I_{D} = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see Figure 14; see Figure 15 $I_{D} = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$ $I_{D} = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see Figure 14; see Figure 15 $I_{D} = 10 \text{ A}; V_{DS} = 15 \text{ V}; \text{see Figure 14};$ see Figure 15 $V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	- - - -	9 1.5 1.1 0.4 1.4 2.5 641	- - - -	nC nC nC nC V
Q _{GS} (th) Q _{GS} (th-pl) Q _{GD} V _{GS} (pl) C _{iss} C _{oss} C _{rss}	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance output capacitance	$\begin{split} &I_{D} = 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V};\\ &\text{see Figure 14}; \text{ see Figure 15}\\ &I_{D} = 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V}\\ &I_{D} = 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V};\\ &\text{see Figure 14}; \text{ see Figure 15}\\ \end{split}$	- - - - - - -	9 1.5 1.1 0.4 1.4 2.5 641 146	- - - - - -	nC nC nC nC V V
Q _{GS} (th) Q _{GS} (th-pl) Q _{GD} V _{GS} (pl) C _{iss} C _{oss} C _{rss}	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance output capacitance reverse transfer capacitance	$\begin{split} & I_D = 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \\ & \text{see Figure 14}; \text{ see Figure 15} \\ & I_D = 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V} \\ & I_D = 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V}; \\ & \text{see Figure 14}; \text{ see Figure 15} \\ & I_D = 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ see Figure 15} \\ & I_D = 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ see Figure 14}; \\ & \text{see Figure 15} \\ & V_{DS} = 15 \text{ V}; \text{ V}_{GS} = 0 \text{ V}; \text{ f} = 1 \text{ MHz}; \\ & \text{T}_j = 25 \text{ °C}; \text{ see Figure 16} \end{split}$	- - - - - - - - -	9 1.5 1.1 0.4 1.4 2.5 641 146 46	- - - - -	nC nC nC nC V pF pF
Q _{GS} Q _{GS} (th) Q _{GS} (th-pl) Q _{GD} V _{GS} (pl) C _{iss} C _{oss} C _{rss} t _d (on) t _r t _d (off)	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance output capacitance reverse transfer capacitance turn-on delay time	$\begin{split} &I_{D} = 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V};\\ &\text{see Figure 14}; \text{ see Figure 15}\\ &I_{D} = 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V}\\ &I_{D} = 10 \text{ A}; \text{ V}_{DS} = 15 \text{ V}; \text{ V}_{GS} = 4.5 \text{ V};\\ &\text{see Figure 14}; \text{ see Figure 15}\\ \end{split}$	- - - - - - - - - -	9 1.5 1.1 0.4 1.4 2.5 641 146 46 13.4	- - - - - - - -	nC nC nC nC V V pF pF pF

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Product data sheet

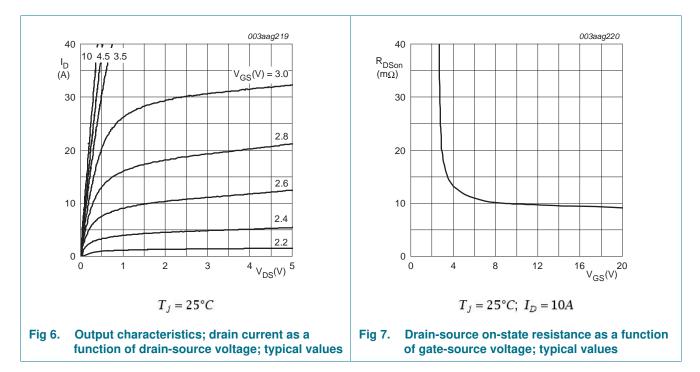
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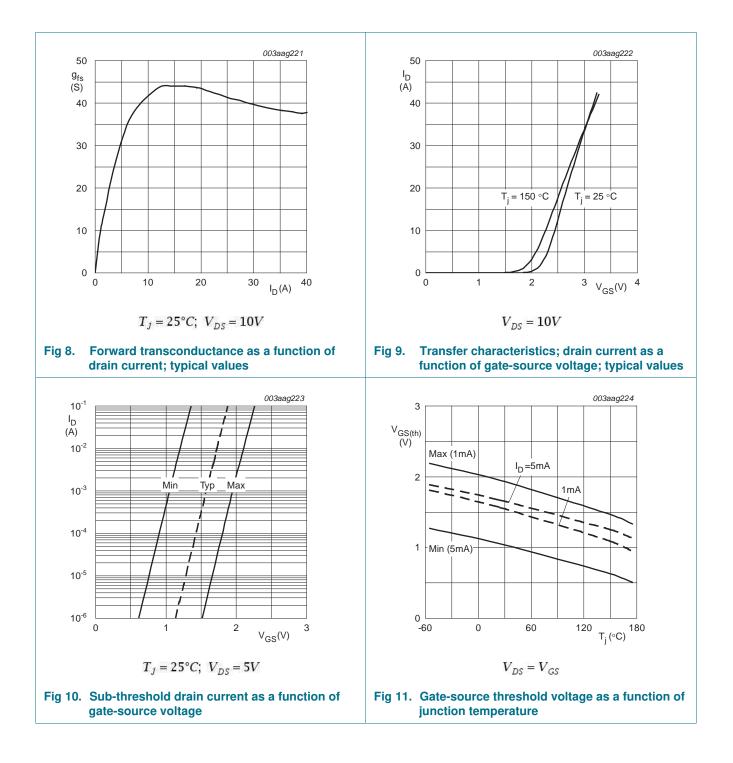
N-channel 30 V 11.6 m Ω logic level MOSFET in LFPAK using NextPower technology

Table 6. Characteristics ...continued

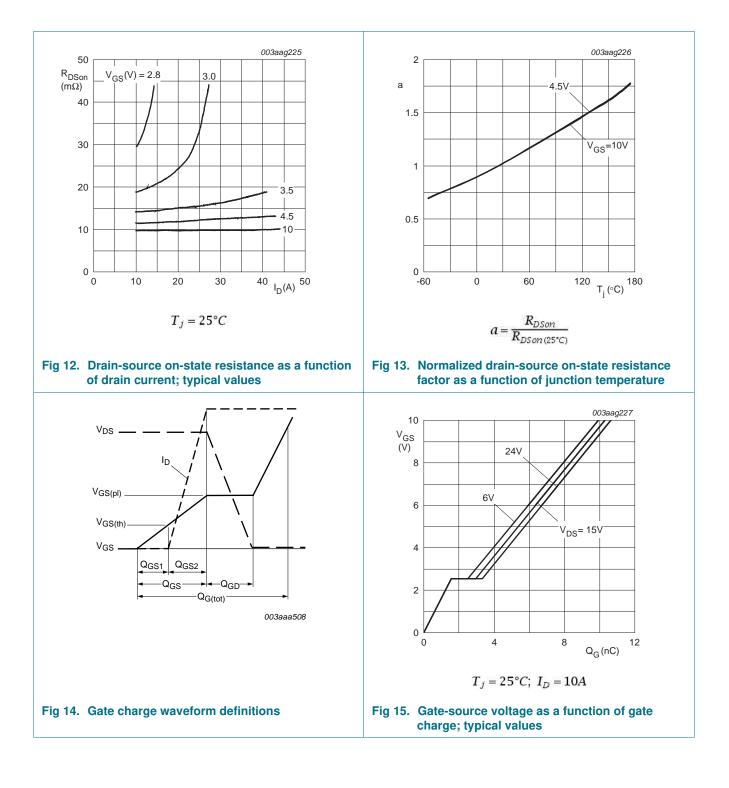
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{oss}	output charge	V_{GS} = 0 V; V_{DS} = 15 V; f = 1 MHz; T _j = 25 °C	-	3.8	-	nC
Source-dra	in diode					
V_{SD}	source-drain voltage	I _S = 10 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.85	1.1	V
t _{rr}	reverse recovery time	$I_{S} = 10 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$	-	17	-	ns
Q _r	recovered charge	$V_{GS} = 0 V; V_{DS} = 15 V$	-	7	-	nC
t _a	reverse recovery rise time	$V_{GS} = 0 V; I_S = 10 A;$	-	10	-	ns
t _b	reverse recovery fall time	dl _S /dt = -100 A/μs; V _{DS} = 15 V; see <u>Figure 18</u>	-	7	-	ns



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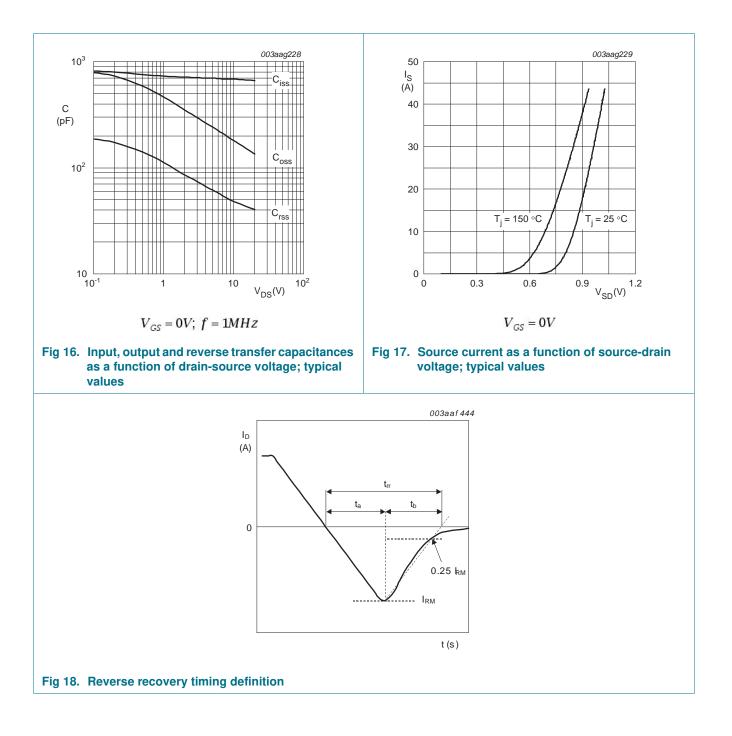


PSMN011-30YLC



PSMN011-30YLC Product data sheet

PSMN011-30YLC



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7. Package outline

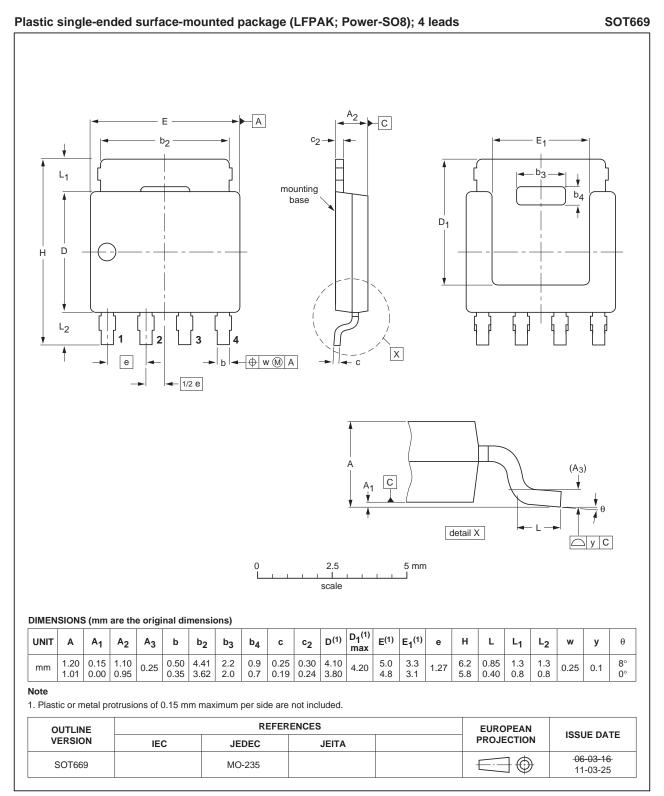


Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

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8. Revision history

Table 7. Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN011-30YLC v.3	20111024	Product data sheet	-	PSMN011-30YLC v.2
Modifications:	 Data sheet sta 	tus changed from prelimina	ry to product.	
	 Various change 	es to content.		
PSMN011-30YLC v.2	20110930	Preliminary data shee	·t -	PSMN011-30YLC v.1

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without Nexperia's warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond Nexperia's specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies Nexperia for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond Nexperia's standard warranty and Nexperia's product specifications.

9.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

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N-channel 30 V 11.6 mΩ logic level MOSFET in LFPAK using NextPower technology

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